

isc N-Channel MOSFET Transistor

2SK538

DESCRIPTION

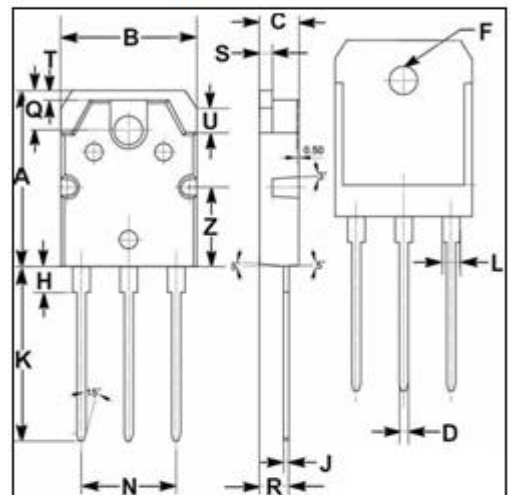
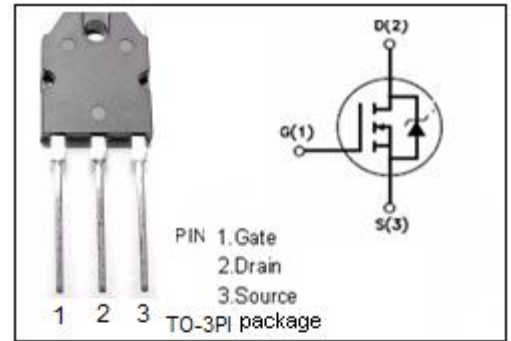
- Drain Current  $-I_D=3A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=900V(\text{Min})$

APPLICATIONS

- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	3	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	100	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

**isc N-Channel Mosfet Transistor****2SK538****• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	900			V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> = 1mA	1.5		3.5	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =1.5A		4.5		Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =900V; V <sub>GS</sub> = 0			300	uA